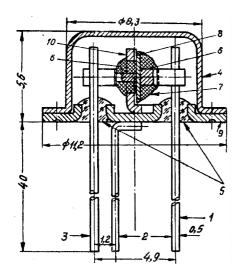
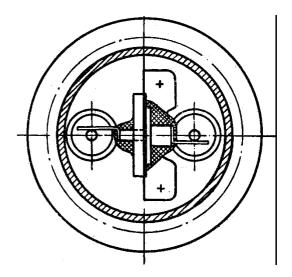
П6А, П6Б. П6В, П6Г, П6Д

Low frequency germanium alloy p-n-p transistors. Intended for use in output stages and switching circuits. Packaged in welded metal can with glass insulator and radiator.





	Nominal electrical characteristics
Frequency limit for current amplification	1 00
П6А	> 100 kHz
П6Б, П6В, П6Д	> 465 kHz
П6Г	> 1000 kHz
Current gain, common base topology	
П6А, П6Д	> 0,9
П6Б	0,900,94
П6В	> 0,94 (0,995)*
П6Г	> 0,97
Current gain, common emitter topolo	gy
П6А, П6Д	> 9
П6Б	915
П6В	1549
П6Г	> 32
Power gain	
П6А	> 30 dB (35 dB)*
П6Б, П6В, П6Д	> 34 dB (38 dB)*
П6Г	> 37 dB (40 dB)*
Collector's reverse current	,
П6А	< 30 μA (20 μA)*
П6Б – П6Д	< 15 μA (10 μA)*
Emitter's reverse current	
П6А	< 30 μΑ
П6Б – П6Д	< 15 μA
Input resistance	2535 Ohm (40 Ohm)*
Output conductance	,
П6А, П6Г	< 3,3 μmho
П6Б, П6В, П6Д	< 2 μmho (1 μmho)*
Voltage feedback coefficient	r - (r - /
П6А	$< 5x10^{-3}$
П6Б – П6Д	$<6x10^{-4}(2,5x10^{-4})*$
Collector capacitance	
П6А	< 30 pF (40 pF)*
П6Б – П6Д	< 50 pF (40 pF)*
Noise coefficient	30 pr (10 pr)
П6А - П6Г	< 33 dB (22 dB)*
П6Д	< 12 dB
Lifespan	5000 h
Thermal resistance	0,5 °C/mW
i incrinui resistance	0,5 0/111 77

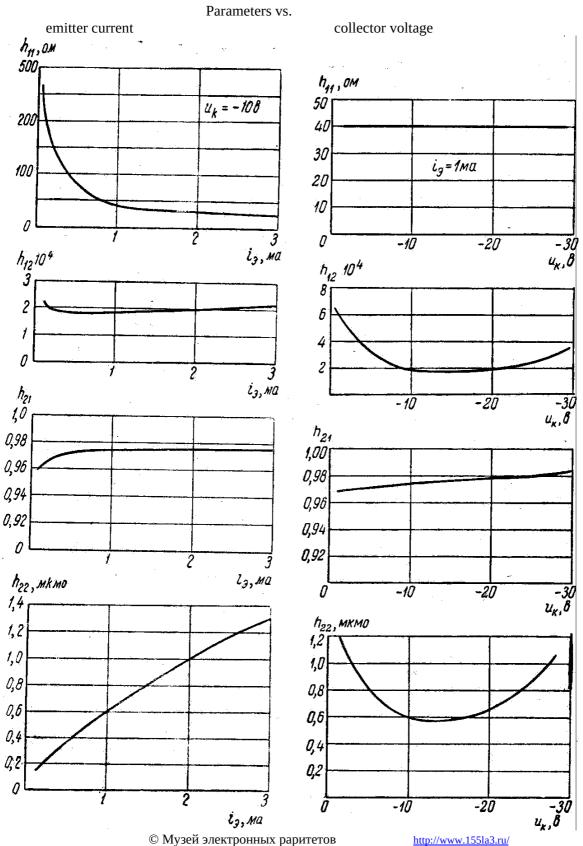
* according to some sources

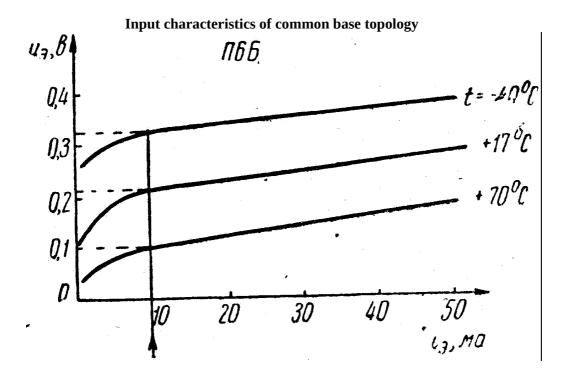
Absolute Maximum Ratings

Collector amplification current
Collector switching current
Collector voltage
Power dissipation
Ambient temperature
Collector temperature
Sustained vibration
Repeated shocks with acceleration
* according to some sources

30 mA (10 mA)* 100 mA (50 mA)* 30 V (15 V)* 150 mW -50...+60 °C -60 ...+100 °C 12 g 100 g







Collector junction temperature, °C vs dissipated power, mW

